

## THE SPECIFICATION OF AlGaAs IR LED CHIP “YL-C850-MH”

### 1. DESCRIPTION

This is a AlGaAs Infrared LED chip. It is P-side up. The peak wavelength is 850 nm (Typ.).

### 2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25°C)

CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage ( Vf ) IF=16mA		1.8		V
Reverse Current ( Ir ) Vr=6V			10	uA
Radiated Power <sup>1)</sup> (Po) IF=16mA		0.8		mW
Peak Wavelength ( λ p ) IF=16mA		850		nm

1) LED chip is mounted on TO-18 gold header without resin coated.

### 3. ABSOLUTE MAXIMUM RATINGS

Continuous Maximum Forward Current : 30 mA(DC)  
Reverse Voltage : 6 V(IR=10 μ A)

### 4. PHYSICAL CHARACTERISTICS AND STRUCTURE

- 1) Material : AlGaAs
- 2) Structure : Double Hetero Structure
- 3) Junction Size : 0.190mm × 0.330mm
- 4) Thickness : 0.280mm
- 5) Emission area : 0.080mm diameter
- 6) Anode Metallization : Gold Alloy
- 7) Cathode Metallization: Gold Alloy

## Physical Dimensions

Model YL-C850-MH

UNIT:um

